

TLP3041(S),TLP3042(S),TLP3043(S)

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
TRIAC DRIVER
SOLID STATE RELAY

The TOSHIBA TLP3041 (S), TLP3042 (S), TLP3043 (S) consist of a zero voltage crossing turn-on photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

All parameters are tested to the specification of TLP3041, TLP3042, TLP3043.

- Peak Off-State Voltage : 400 V (min)
- Trigger LED Current : 15 mA (max) (TLP3041)
10 mA (max) (TLP3042)
5 mA (max) (TLP3043)
- On-State Current : 100 mA (max)
- UL Recognized : UL1577, File No. E67349
- Isolation Voltage : 5000 Vrms (min)
- Option (D4) Type VDE Approved : DIN VDE0884 / 06.92
Certificate No. 68329

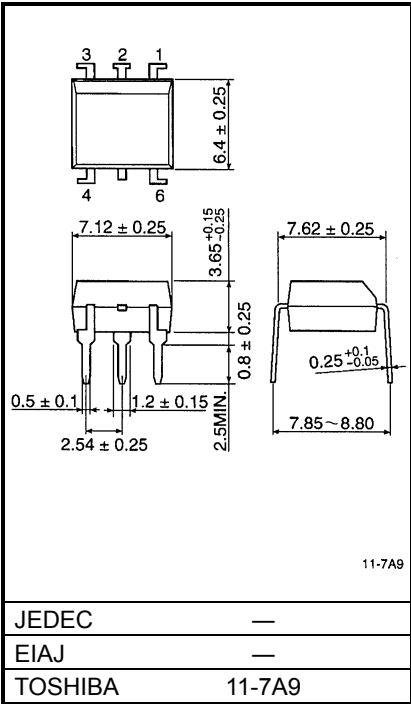
Maximum Operating Insulation Voltage : 890 Vpk
Highest Permissible Over Voltage : 8000 Vpk

Note: When a VDE0884 approved type is needed,please designate the “Option (D4)”

- Device Construction

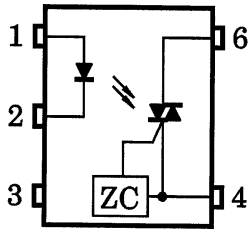
	7.62mm pich standard type	10.16 mm pich (LF2) type
Creepage Distance	7.0 mm (min)	8.0 mm (min)
Clearance	7.0 mm (min)	8.0 mm (min)
Insulation Thickness	0.5 mm (min)	0.5 mm (min)

Unit: mm



weight: 0.39g

PIN CONFIGURATION
(Top view)



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT
LED	Forward Current		I _F	50	mA
	Forward Current Derating (Ta ≥ 53°C)		ΔI _F / °C	−0.7	mA / °C
	Peak Forward Current (100μs pulse, 100pps)		I _{FP}	1	A
	Power Dissipation		P _D	100	mW
	Power Dissipation Derating (Ta ≥ 25°C)		ΔP _D / °C	−1.0	mW / °C
	Reverse Voltage		V _R	5	V
	Junction Temperature		T _j	125	°C
DETECTOR	Off-State Output Terminal Voltage		V _{DRM}	400	V
	On-Stage RMS	Ta = 25°C	I _{T(RMS)}	100	mA
	Current	Ta = 70°C		50	
	On-State Current Derating (Ta ≥ 25°C)		ΔI _T / °C	−1.1	mA / °C
	Peak On-Stage Current (100μs pulse, 120pps)		I _{TP}	2	A
	Peak Nonrepetitive Surge Current (P _W = 10ms, DC = 10%)		I _{TSM}	1.2	A
	Power Dissipation		P _D	300	mW
	Power Dissipation Derating (Ta ≥ 25°C)		ΔP _D / °C	−4.0	mW / °C
	Junction Temperature		T _j	115	°C
Storage Temperature Range			T _{stg}	−55 ~ 150	°C
Operating Temperature Range			T _{opr}	−40 ~ 100	°C
Lead Soldering Temperature (10s)			T _{sol}	260	°C
Total Package Power Dissipation			P _T	330	mW
Total Package Power Dissipation Derating (Ta ≥ 25°C)			ΔP _T / °C	−4.4	mW / °C
Isolation Voltage (AC, 1 min., R.H. ≤ 60%) (Note 1)			BV _S	5000	Vrms

Note 1: Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN	TYP.	MAX	UNIT
Supply Voltage	V_{AC}	—	—	120	Vac
Forward Current	I_F^*	15	20	25	mA
Peak On-Stage Current	I_{TP}	—	—	1	A
Operating Temperature	T_{opr}	-25	—	85	°C

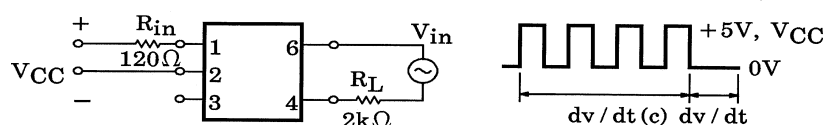
* : In the case of TLP3042

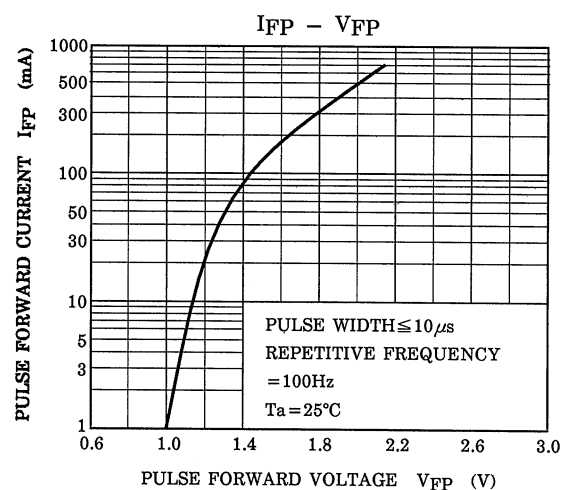
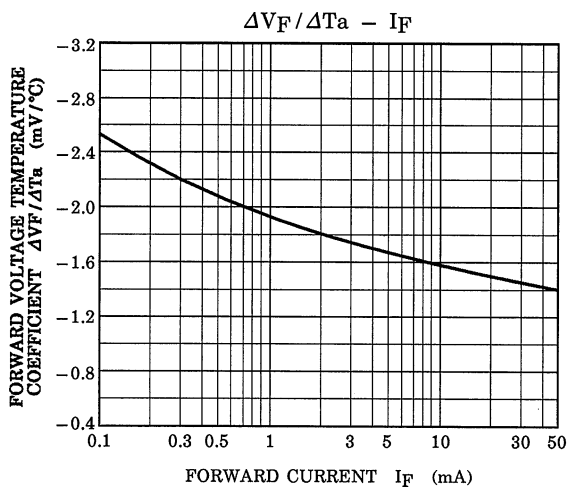
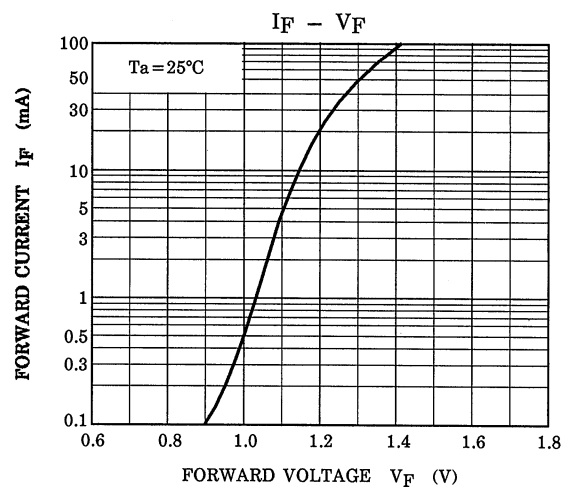
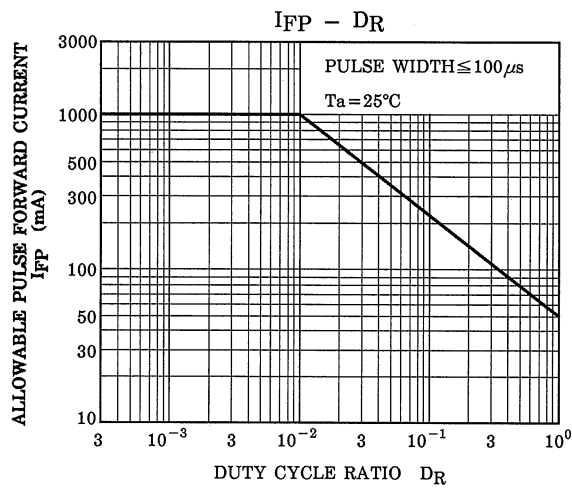
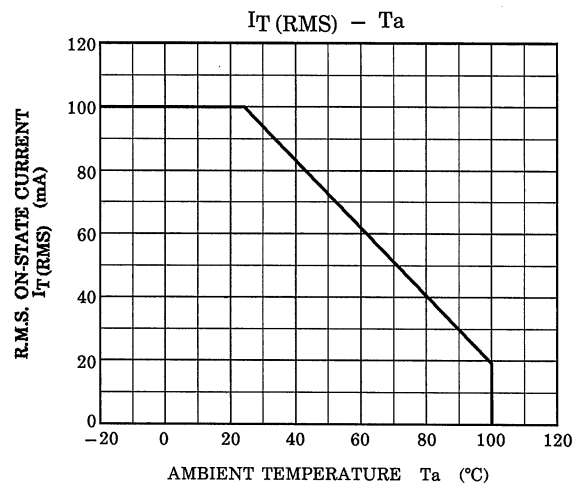
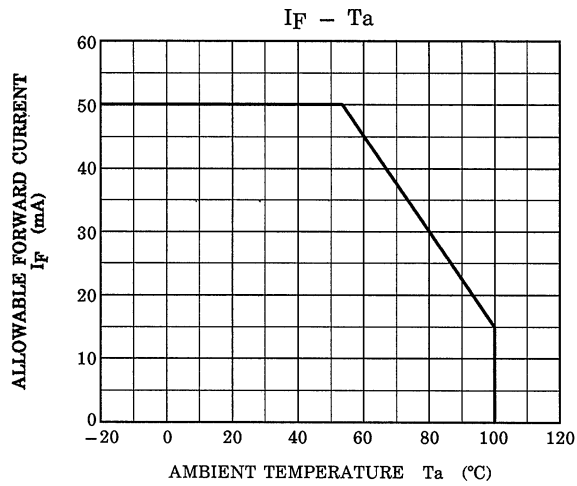
INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

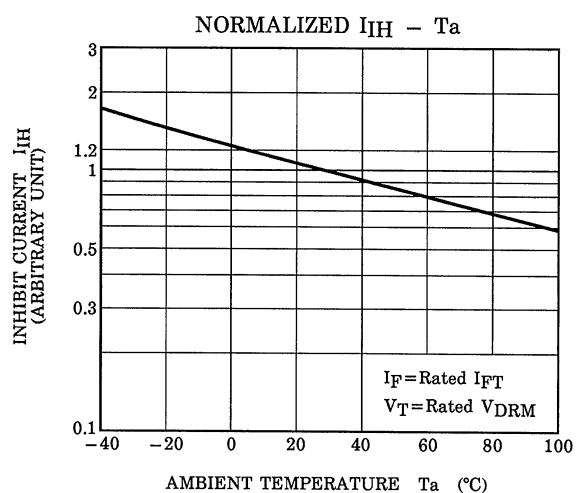
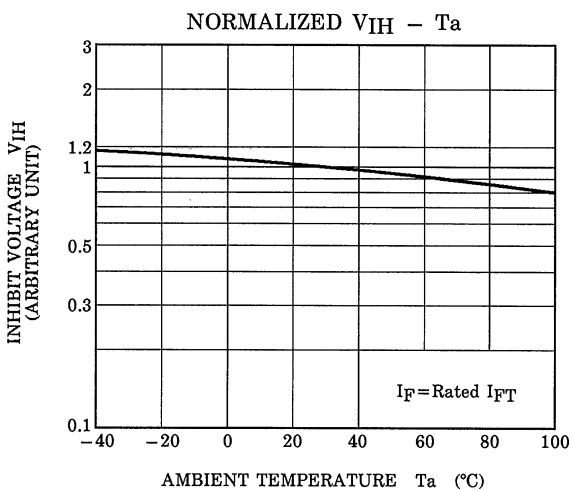
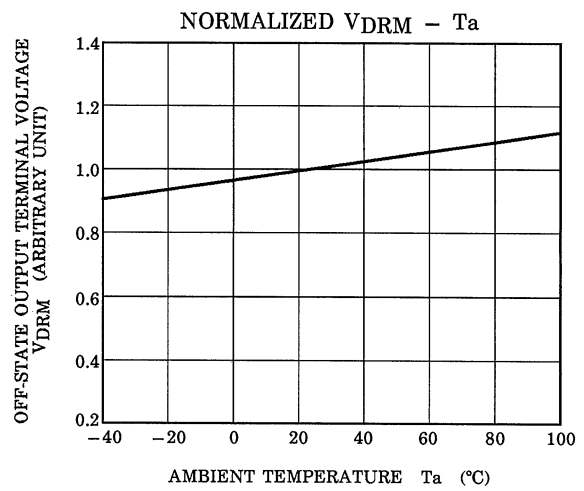
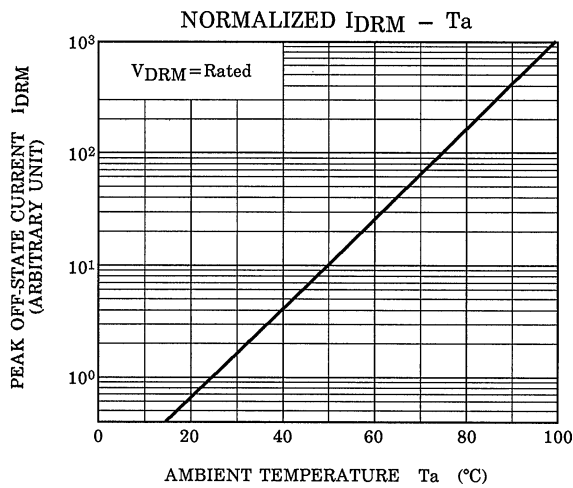
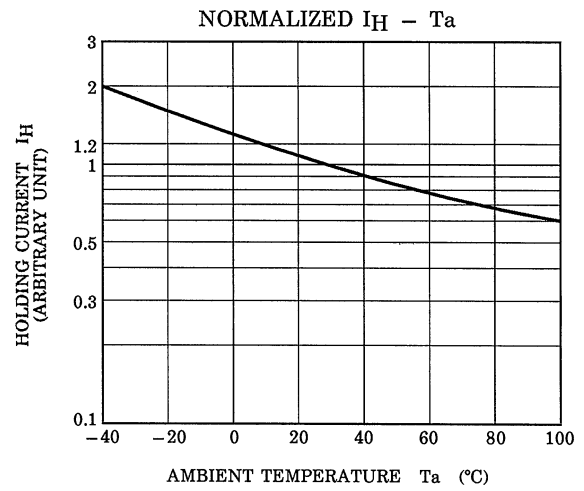
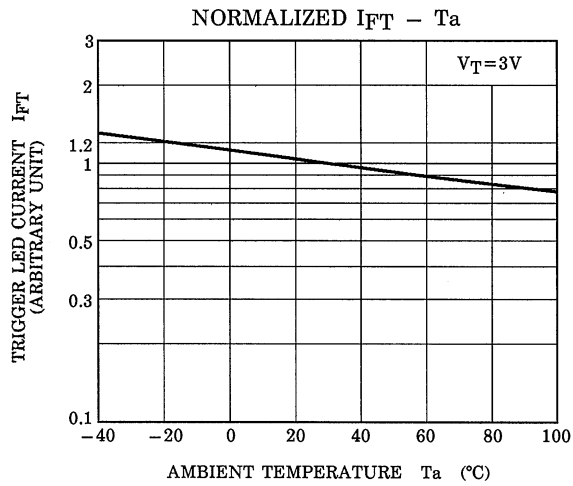
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	10	—	pF
DETECTOR	Peak Off-State Current	I_{DRM}	$V_{\text{DRM}} = 400\text{V}$	—	10	100	nA
	Peak On-Stage Voltage	V_{TM}	$I_{\text{TM}} = 100\text{mA}$	—	1.7	3.0	V
	Holding Current	I_H	—	—	0.6	—	mA
	Critical Rate of Rise of Off-State Voltage	dv / dt	$V_{\text{in}} = 120\text{Vrms}, T_a = 85^\circ\text{C}$ (Fig.1)	200	500	—	V / μs
	Critical Rate of Rise of Commutating Voltage	$dv / dt(c)$	$V_{\text{in}} = 30\text{Vrms}, I_T = 15\text{mA}$ (Fig.1)	—	0.2	—	V / μs

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Trigger LED Current	TLP3041	I_{FT}	$V_T = 3\text{V}$	—	—	15	mA
	TLP3042			—	5	10	
	TLP3043			—	—	5	
Inhibit Voltage		V_{IH}	$I_F = \text{Rated } I_{\text{FT}}$	—	—	40	V
Leakage in Inhibited State		I_{IH}	$I_F = \text{Rated } I_{\text{FT}}$ $V_T = \text{Rated } V_{\text{DRM}}$	—	100	300	μA
Capacitance Input to Output		C_S	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance		R_S	$V_S = 500\text{V}$ (R.H. $\leq 60\%$)	5×10^{10}	10^{14}	—	Ω
Isolation Voltage		BV_S	AC, 1 minute	5000	—	—	Vrms
			AC, 1 second (in oil)	—	10000	—	
			DC, 1 minute (in oil)	—	10000	—	Vdc

Fig. 1 dv / dt TEST CIRCUIT






RESTRICTIONS ON PRODUCT USE

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